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RLT6650G TECHNICAL DATA



High Power Visible Laserdiode

Structure: **High Efficiency MOVCD Quantum Well Design**

Lasing wavelength: **660 nm typ., multimode**

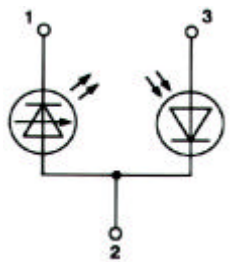
Output power: **50 mW**

Package: **9 mm**

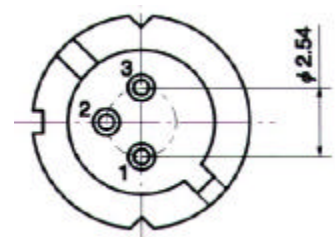


NOTE!
LASERDIODE
MUST BE COOLED!

PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Absolute Maximum Ratings (T_c=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P _o	55	mW
LD Reverse Voltage	V _{R(LD)}	2	V
PD Reverse Voltage	V _{R(PD)}	30	V
Operating Temperature	T _C	-10 .. +40	°C
Storage Temperature	T _{STG}	-40 .. +85	°C

Optical-Electrical Characteristics (T_c = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P _o	cw operation		50		mW
Threshold Current	I _{th}	cw operation	70	85	120	mA
Operation Current	I _{op}	P _o = 50 mW	135	160	220	mA
Operation Voltage	V _{op}	P _o = 50 mW	2.0	2.1	2.2	V
Lasing Wavelength	λ _p	P _o = 50 mW	655	660	665	nm
Beam Divergence	θ	P _o = 50 mW	10	12	14	°
Beam Divergence	θ _⊥	P _o = 50 mW	20	25	30	°
Lasing Aperture	A	P _o = 50 mW		10 x 1		μm ²
Monitor Current	I _m	P _o = 50 mW	0.35	0.5	1.5	mA